

We Claim:

1. A test structure for determining a short circuit between trench capacitors in a memory cell array wherein the trench capacitors are arranged in matrix form, the test structure comprising:

at least one of tunnel structures and bridge structures connecting the trench capacitors of two rows of trench capacitors to one another to form trench capacitor rows; and

a contact area for contact connection provided at each end section of each of said trench capacitor rows.

2. The test structure according to claim 1, wherein said two rows of interconnected trench capacitors are formed within a regular trench capacitor matrix.

3. The test structure according to claim 1, wherein at least one further row of non-connected trench capacitors is disposed between said two rows of interconnected trench capacitors.